

Most Frequently Occurring Classifications of Patents Returned
From A Search of 10/605,198 on July 12, 2004

Combined Classifications

12 365/185.18
12 365/185.22
11 257/E21.682
11 257/E27.103
10 438/264
7 365/185.3
6 365/185.24
6 365/185.29
6 438/257
5 257/316
5 365/185.33
4 257/E21.209
4 365/185.12
3 257/314
3 257/321
3 257/E21.688
3 257/E29.129
3 365/185.16
3 438/261
3 438/262
3 438/529
3 438/593
3 438/594
2 257/315
2 257/E21.312
2 257/E21.68
2 257/E21.685
2 257/E21.687
2 257/E21.689
2 257/E27.081
2 257/E29.214
2 365/182
2 365/185.01
2 365/185.02
2 365/185.09
2 365/185.11
2 365/185.19
2 365/185.21
2 365/185.23
2 365/185.28
2 365/189.02
2 365/189.05
2 365/189.09
2 365/218
2 365/230.08
2 365/238.5
2 438/263
2 438/265
2 438/266
2 438/701

12 365/185.18 (3 OR, 9 XR)

Class 365 : STATIC INFORMATION STORAGE AND RETRIEVAL

365/185.01 FLOATING GATE

365/185.18 .Particular biasing

12 365/185.22 (4 OR, 8 XR)

Class 365 : STATIC INFORMATION STORAGE AND RETRIEVAL

365/185.01 FLOATING GATE

365/185.18 .Particular biasing

365/185.2 ..Reference signal (e.g., dummy cell)

365/185.22 ...Verify signal

10 438/264 (7 OR, 3 XR)

Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS

438/142 MAKING FIELD EFFECT DEVICE HAVING PAIR OF
ACTIVE REGIONS SEPARATED BY GATE STRUCTURE BY FORMATION

OR

438/197 ALTERATION OF SEMICONDUCTIVE ACTIVE REGIONS
.Having insulated gate (e.g., IGFET, MISFET,
MOSFET, etc.)

438/257 ..Having additional gate electrode surrounded
by dielectric (i.e., floating gate)

438/264 ...Tunneling insulator

7 365/185.3 (1 OR, 6 XR)

Class 365 : STATIC INFORMATION STORAGE AND RETRIEVAL

365/185.01 FLOATING GATE

365/185.18 .Particular biasing

365/185.29 ..Erase

365/185.3 ...Over erasure

6 365/185.24 (1 OR, 5 XR)

Class 365 : STATIC INFORMATION STORAGE AND RETRIEVAL

365/185.01 FLOATING GATE

365/185.18 .Particular biasing

365/185.24 ..Threshold setting (e.g., conditioning)

6 365/185.29 (3 OR, 3 XR)

Class 365 : STATIC INFORMATION STORAGE AND RETRIEVAL

365/185.01 FLOATING GATE

365/185.18 .Particular biasing

365/185.29 ..Erase

6 438/257 (3 OR, 3 XR)

Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS

438/142 MAKING FIELD EFFECT DEVICE HAVING PAIR OF
ACTIVE REGIONS SEPARATED BY GATE STRUCTURE BY FORMATION

OR

438/197 ALTERATION OF SEMICONDUCTIVE ACTIVE REGIONS
.Having insulated gate (e.g., IGFET, MISFET, MOSFET, etc.)

438/257 ..Having additional gate electrode surrounded by dielectric (i.e., floating
gate)

5 257/316 (1 OR, 4 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/264 ...Enhancement mode or with high resistivity
 channel (e.g., doping of 10^{15} cm⁻³ or less)
257/288 .Having insulated electrode (e.g., MOSFET, MOS diode)
257/314 ..Variable threshold (e.g., floating gate memory device)
257/315 ...With floating gate electrode
257/316 With additional contacted control electrode

5 365/185.33 (1 OR, 4 XR)

Class 365 : STATIC INFORMATION STORAGE AND RETRIEVAL

365/185.01 FLOATING GATE
365/185.18 .Particular biasing
365/185.29 ..Erase
365/185.33 ...Flash

PLUS Search Results for S/N 10/605,198, Searched July 12, 2004 (Top 50)

The Patent Linguistics Utility System (PLUS) is a USPTO automated search system for U.S. Patents from 1971 to the present. PLUS is a query-by-example search system which produces a list of patents that are most closely related linguistically to the application searched. This search was prepared by the staff of the Scientific and Technical Information Center, SIRA.

6200859	6055184	6261905	6368976	5949715
5635416	6071779	6356480	6646301	5959894
5773861	6087220	6466484	5753525	5991200
6037223	6133096	5593562	5191556	6016273
6444554	6215147	6228718	5369609	6157576
6461916	6221718	6009013	5475634	6181600
6630392	6215147	5312781	6122200	4780750
5379089	6221718	5877054	5781476	5185718
5443999	6233177	6101128	5844842	5233562
5526307	6240021	RE37199	5917752	